

2MBI450VX-170-50

IGBT Modules

Power Module (V series)
1700V / 450A / 2-in-1 package

■ Features

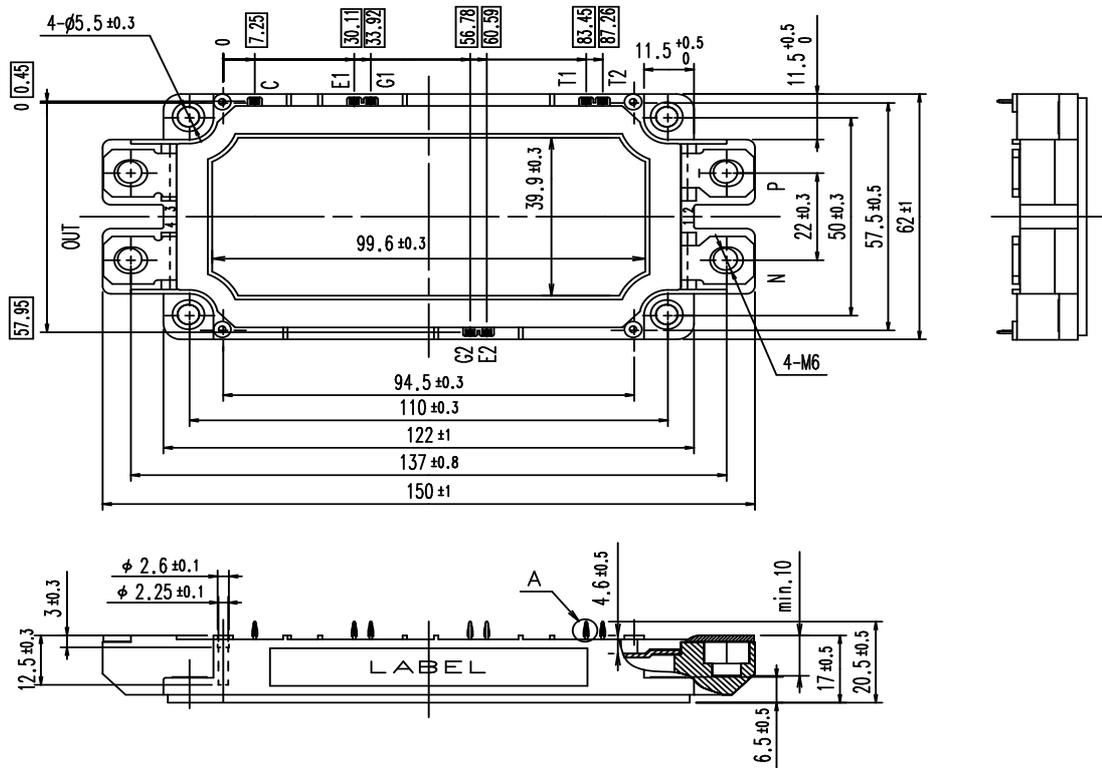
- Low $V_{CE(sat)}$
- Low Inductance Module structure
- Solderless press-fit terminals

■ Applications

- Inverter for Motor Drives, AC and DC Servo Drives
- Uninterruptible Power Supply Systems, Wind Turbines, PV Power Conditioning Systems

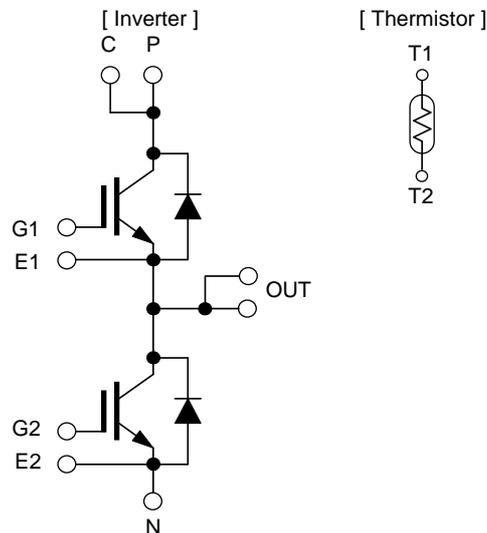


■ Outline drawing (Unit : mm)



NOTE) MARKED SIDE WITH A TOLERANCE OF ± 0.5 Weight: 350g (typ.)

■ Equivalent Circuit



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■ Absolute Maximum Ratings (at $T_C = 25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions	Maximum Ratings	Units	
Collector-Emitter voltage		V_{CES}		1700	V	
Gate-Emitter voltage		V_{GES}		± 20	V	
Collector current	I_C		Continuous	$T_C = 25^\circ\text{C}$	600	A
				$T_C = 100^\circ\text{C}$	450	
	I_C pulse	1ms		900		
	$-I_C$			450		
	$-I_C$ pulse	1ms		900		
Collector power dissipation		P_C	1 device	2500	W	
Junction temperature		T_j		175	°C	
Operating junction temperature (under switching conditions)		T_{jop}		150		
Case temperature		T_C		125		
Storage temperature		T_{stg}		-40 ~ 125		
Isolation voltage	between terminal and copper base (*1)	V_{iso}	AC: 1min.	3400	VAC	
	between thermistor and others (*2)					
Screw Torque	Mounting (*3)	-		3.5	N m	
	Terminals (*4)	-		4.5		

(*1) All terminals should be connected together during the test.

(*2) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

(*3) Recommendable Value : 2.5-3.5 Nm (M5)

(*4) Recommendable Value : 3.5-4.5 Nm (M6)

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■ Electrical characteristics (at T_j= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage Collector current	I _{CES}	V _{GE} =0V, V _{CE} =1700V	-	-	3.0	mA	
Gate-Emitter leakage current	I _{GES}	V _{CE} =0V, V _{GE} =±20V	-	-	600	nA	
Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} =20V, I _C =450mA	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	V _{CE(sat)} (terminal)	V _{GE} = 15V I _C = 450A	T _j =25°C	-	2.65	3.10	V
			T _j =125°C	-	3.10	-	
			T _j =150°C	-	3.15	-	
	V _{CE(sat)} (chip)		T _j =25°C	-	2.00	2.45	
			T _j =125°C	-	2.45	-	
			T _j =150°C	-	2.50	-	
Internal gate resistance	R _{G(int)}	-	-	1.67	-	Ω	
Input capacitance	C _{ies}	V _{CE} =10V, V _{GE} =0V, f=1MHz	-	40	-	nF	
Turn-on time	t _{on}	V _{CC} = 900V I _C = 450A V _{GE} = ±15V R _G = 3.3Ω L _s = 80nH	-	900	-	nsec	
	t _r		-	400	-		
	t _{r(i)}		-	100	-		
Turn-off time	t _{off}		-	1300	-		
	t _f		-	100	-		
Forward on voltage	V _F (terminal)	V _{GE} = 0V I _F = 450A	T _j =25°C	-	2.45	2.90	V
			T _j =125°C	-	2.75	-	
			T _j =150°C	-	2.70	-	
	V _F (chip)		T _j =25°C	-	1.80	2.25	
			T _j =125°C	-	2.10	-	
			T _j =150°C	-	2.05	-	
Reverse recovery time	t _{rr}	I _F = 450A	-	250	-	nsec	
Thermistor Resistance	R	T=25°C	-	5000	-	Ω	
		T=100°C	465	495	520		
Thermistor B value	B	T=25/50°C	3305	3375	3450	K	

5. Thermal resistance characteristics

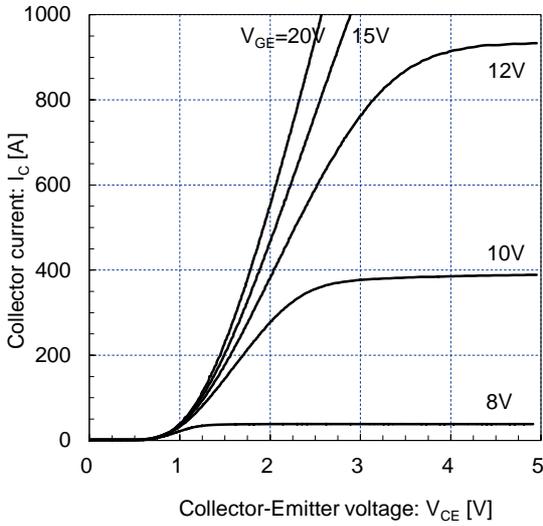
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R _{th(j-c)}	IGBT	-	-	0.06	°C/W
		FWD	-	-	0.10	
Contact thermal resistance (1device) (*1)	R _{th(c-f)}	with thermal compound	-	0.0167	-	

(*1) This is the value which is defined mounting on the additional cooling fin with thermal compound.

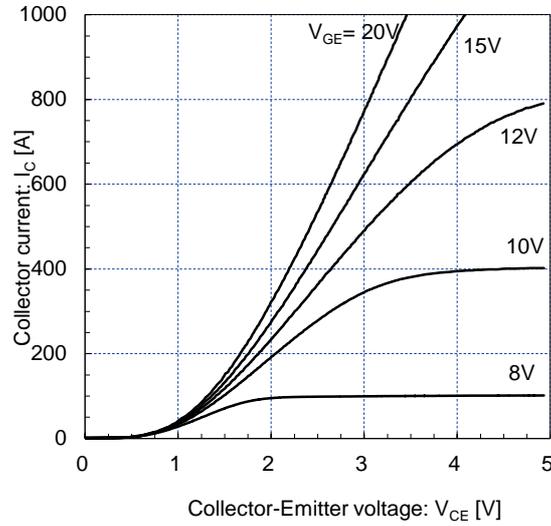
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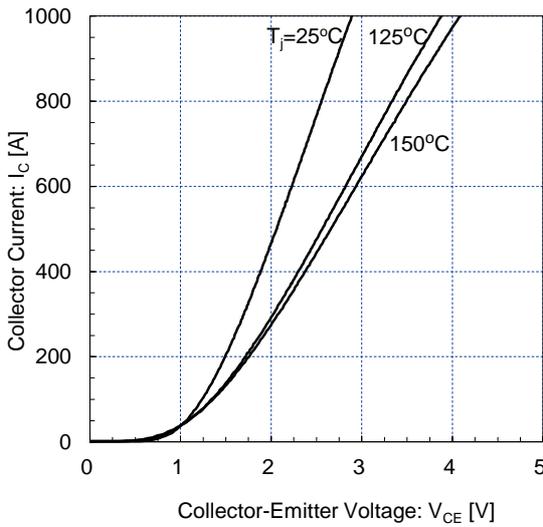
Collector current vs. Collector-Emmitter voltage
 $T_j = 25^\circ\text{C}$ / chip



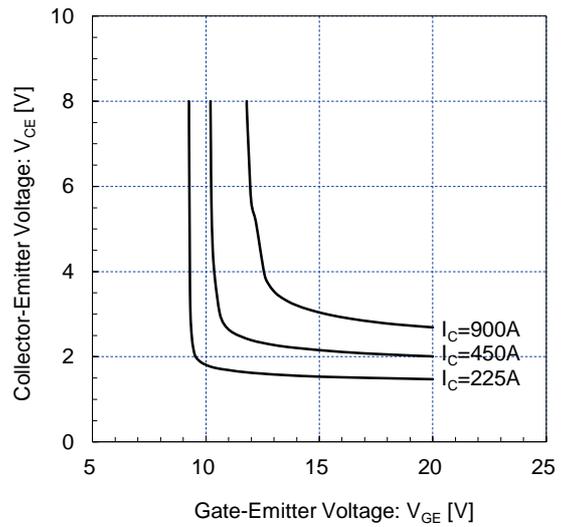
Collector current vs. Collector-Emmitter voltage (typ.)
 $T_j = 150^\circ\text{C}$ / chip



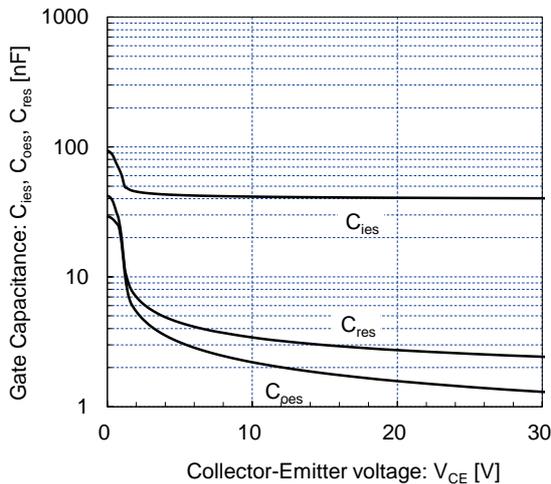
Collector current vs. Collector-Emmitter voltage
 $V_{GE} = 15\text{V}$ / chip



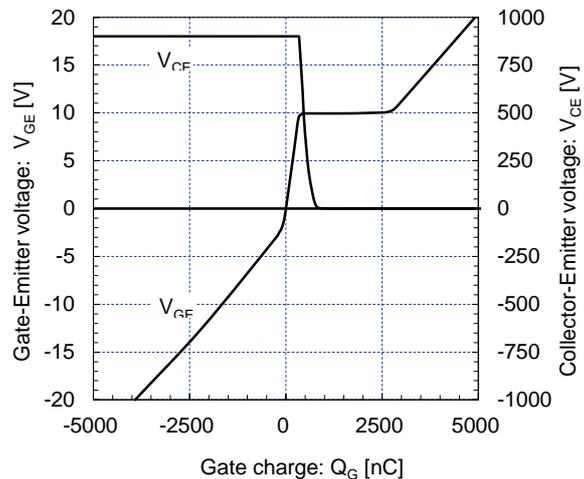
Collector-Emmitter voltage vs. Gate-Emmitter voltage
 $T_j = 25^\circ\text{C}$ / chip



Capacitance vs. Collector-Emmitter Voltage
 $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_j = 25^\circ\text{C}$



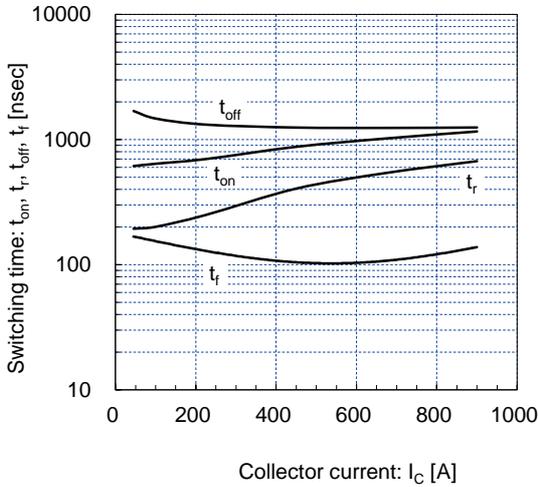
Dynamic Gate Charge (typ.)
 $V_{CC} = 900\text{V}$, $I_C = 450\text{A}$, $T_j = 25^\circ\text{C}$



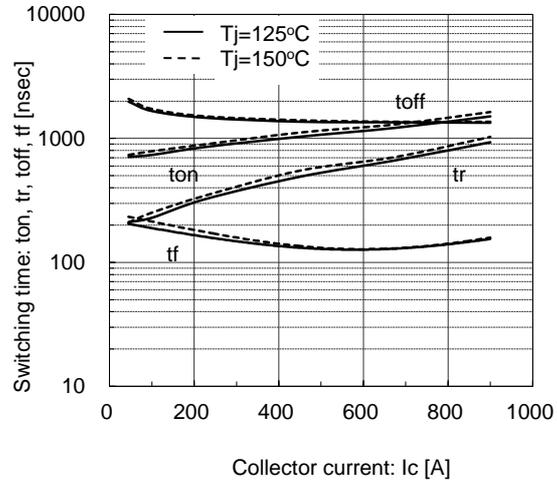
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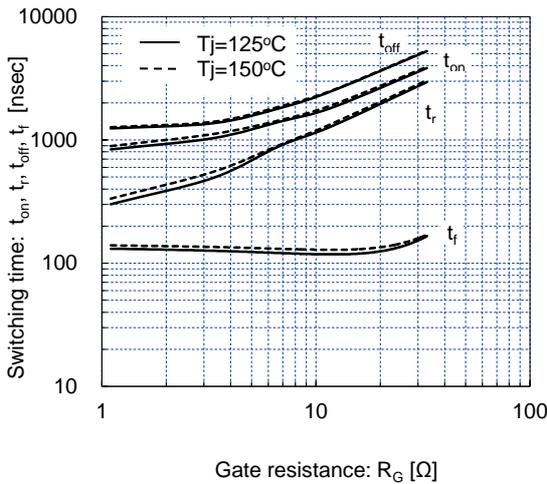
Switching time vs. Collector current (typ.)
 $V_{cc}=900V, V_{GE}=\pm 15V, R_g=3.3\Omega, T_j=25^\circ C$



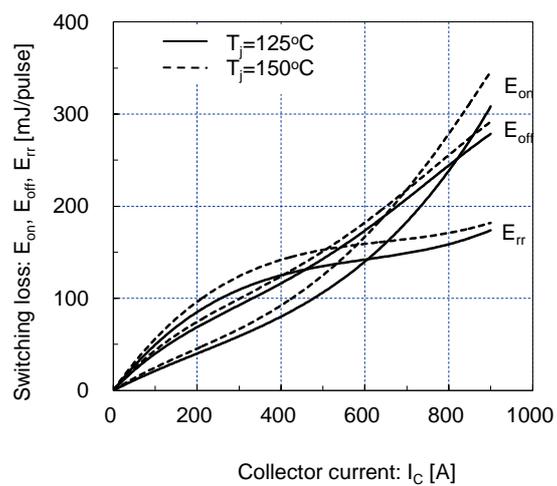
Switching time vs. Collector current (typ.)
 $V_{cc}=900V, V_{GE}=\pm 15V, R_g=3.3\Omega, T_j=125^\circ C, 150^\circ C$



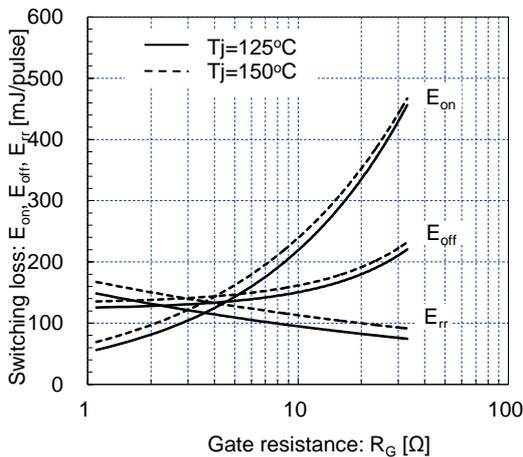
Switching time vs. Gate resistance (typ.)
 $V_{cc}=900V, I_c=450A, V_{GE}=\pm 15V, T_j=125^\circ C, 150^\circ C$



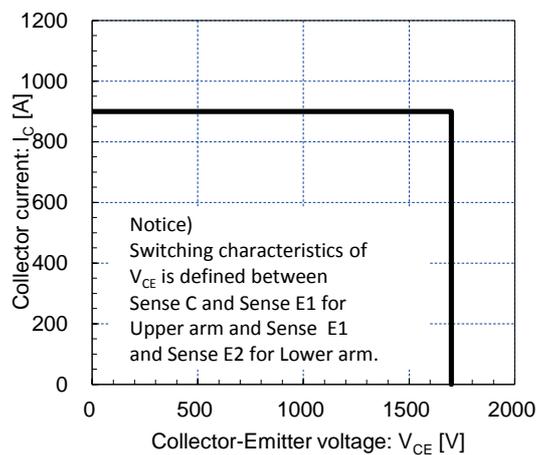
Switching loss vs. Collector current (typ.)
 $V_{cc}=900V, V_{GE}=\pm 15V, R_g=3.3\Omega, T_j=125^\circ C, 150^\circ C$



Switching loss vs. Gate resistance (typ.)
 $V_{cc}=900V, I_c=450A, V_{GE}=\pm 15V, T_j=125^\circ C, 150^\circ C$



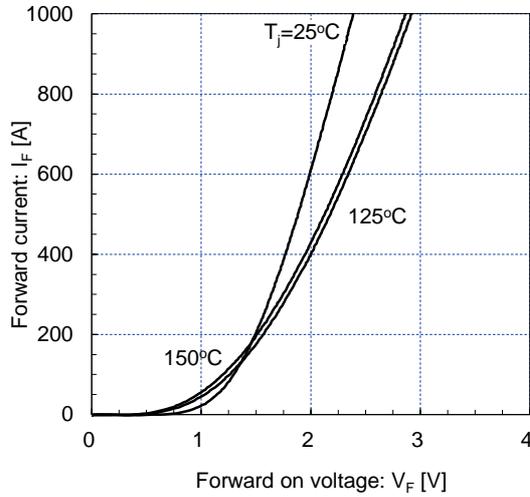
Reverse bias safe operating area (max.)
 $+V_{GE}=15V, -V_{GE}=15V, R_g=3.3\Omega, T_j=150^\circ C$



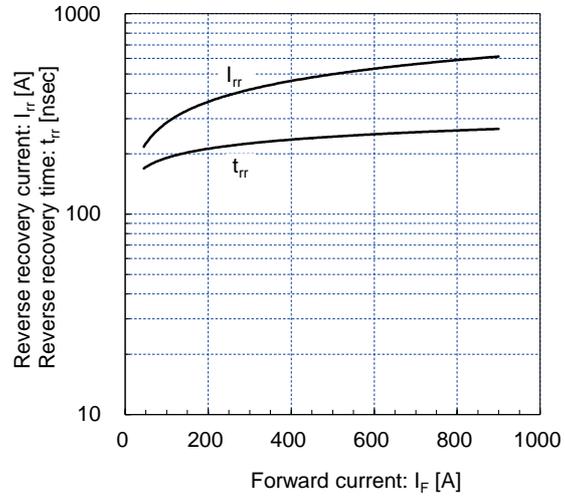
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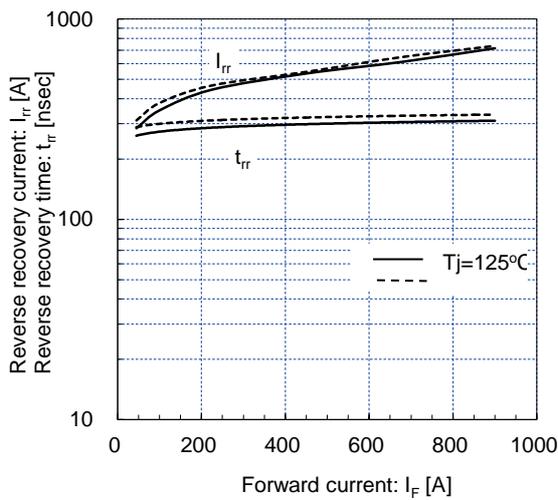
Forward current vs. Forward vltage (typ.)
chip



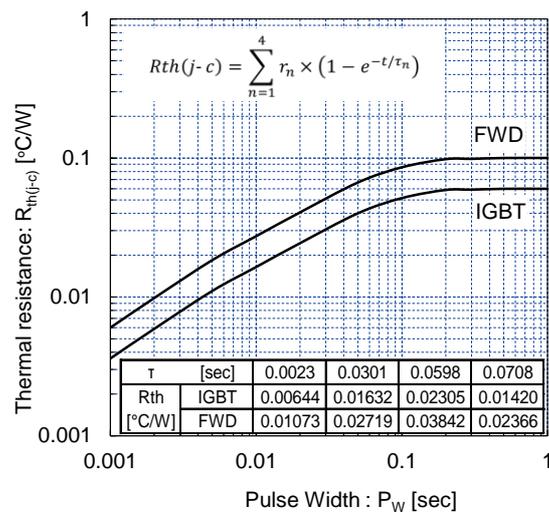
Reverse recovery characteristics (typ.)
 $V_{CC}=900\text{V}$, $V_{GE}=\pm 15\text{V}$, $R_g=3.3\Omega$, $T_j=25^\circ\text{C}$



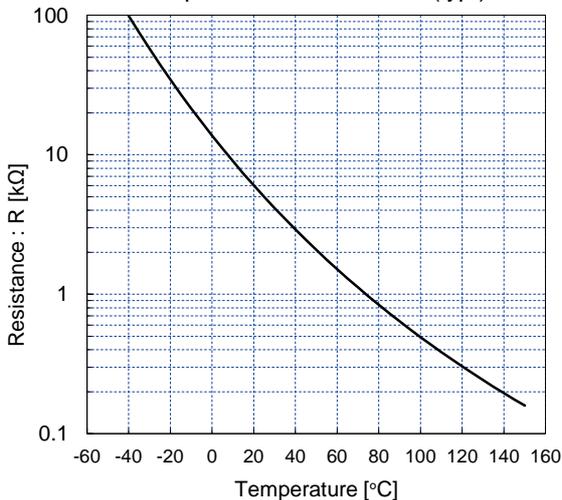
Reverse Recovery Characteristics (typ.)
 $V_{CC}=900\text{V}$, $V_{GE}=\pm 15\text{V}$, $R_g=3.3\Omega$, $T_j=125^\circ\text{C}, 150^\circ\text{C}$



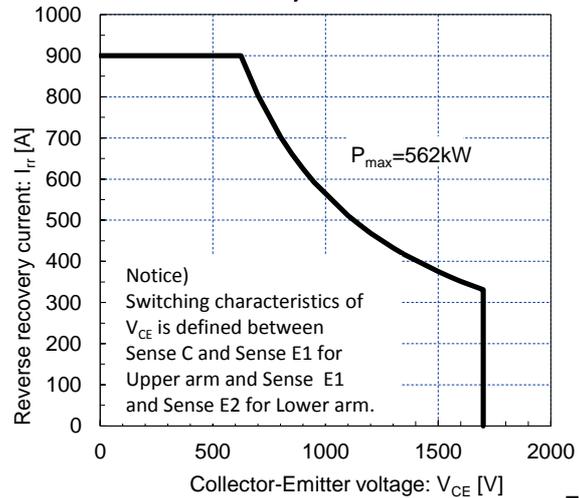
Transient Thermal Resistance (max.)



[THERMISTOR]
Temperature characteristic (typ.)



FWD safe operating area (max.)
 $T_j=150^\circ\text{C}$



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